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PTO  
U.S. PATENT  
09/362804

FORM PTO-1449 (Modified)

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)

Attorney Docket No.: 1126D1/T08910

Applicant: KRAMADHATI V. RAVI et al.

Filing Date: Herewith

Application No.: Unassigned

Group: Unassigned

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Reference Designation		U.S. PATENT DOCUMENTS					
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)	
VB	AA	4,495,218	01/22/85	Azuma et al.	427	53.1	09/22/83
VB	AB	4,732,761	03/22/88	Machida et al.	437	228	03/21/86
VB	AC	4,851,370	07/25/89	Doklan et al.	437	225	12/28/87
VB	AD	4,872,947	10/10/89	Wang et al.	156	643	10/26/88
VB	AE	4,877,641	10/31/89	Dory	427	38	05/31/88
VB	AF	5,000,113	03/19/91	Wang et al.	118	723	12/19/86
VB	AG	5,288,518	02/22/94	Homma	427	255.1	06/05/92
VB	AH	5,314,724	05/24/94	Tsukune et al.	427	489	12/19/91
VB	AI	5,319,247	07/06/94	Matsuura	257	760	10/25/91
VB	AJ	5,429,070	07/04/95	Campbell et al.	118	723 R	11/20/92
VB	AK	5,444,207	08/22/95	Sekine et al.	219	121.43	03/26/93
VB	AL	5,453,305	09/26/95	Lee	427	562	09/02/93
VB	AM	5,710,486	01/20/98	Ye et al.	315	111.21	05/08/95

FOREIGN PATENT DOCUMENTS							
	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)	
VB	AN	WO 92/20833	11/26/92	PCT	C23C	16/00	yes
VB	AO	JP 63-80538	04/11/88	Japan	H01L	21/31	yes (abstract)
VB	AP	JP 2-216851	08/29/90	Japan	H01L	21/90	yes (abstract)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
VB	AQ M. Galiano et al., "Stress-Temperature Behavior of Oxide Films Used For Intermetal Dielectric Applications," 1992 Proceedings 9 <sup>th</sup> International IEEE VLSI Multilevel Interconnection Conference, Santa Clara, California, June 9-10, 1992, British Library Serial No. 4551-700750, pp. 100-106 (June 1992).
VB	AR S. Mizuno et al., "Improved Gap-Filling Capability of Fluorine-Doped PECVD Silicon Oxide Thin Film," Thin Solid Films, vol. 279, pp. 82-86 (1996).
VB	AS K. Musaka et al., "Single Step Gap Filling Technology for Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O <sub>2</sub> Chemical Vapor Deposition System," Extended Abstracts of the 1993 International Conference of Solid State Devices and Materials, Makuhari, pp. 510-512 (1993).
VB	AT S. Robles et al., "Effects of RF Frequency and Deposition Rates on the Moisture Resistance of PECVD TEOS-Based Oxide Films," ECS Extended Abstracts, The Electrochemical Society, Spring Meeting, St. Louis, Missouri, May 17-22, 1992, Abstract No. 129, vol. 92-1, pp. 215-216 (May 1992).
VB	AU D. Webb et al., "Silicon Dioxide Films Produced by PECVD of TEOS and TMCTS," 10439 Proceedings of the Second International Symposium on Ultra Large Scale Integration Science and Technology, ULSI Science and Technology 1989, vol. 89, no. 9, pp. 571-585 (1989).
VB	AV D. Yu et al., "Step Coverage Study of PETEOS Deposition for Intermetal Dielectric Applications," 1990 Proceedings Seventh International IEEE VLSI Multilevel Interconnection Conference, IEEE Catalog No. 90 <sup>TH</sup> 0325-1, Library of Congress No. 89-644090, Santa Clara Marriott Hotel, Santa Clara, CA, June 12-13, 1990, pp. 166-172 (June 1990).

EXAMINER *[Signature]* DATE CONSIDERED 11/10/99

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.